

ABSTRACT OF THE DISCLOSURE

A method of controlling a conductive layer deposition process includes depositing a conductive layer onto a semiconductor wafer based upon a deposition recipe, measuring a thickness of the conductive layer deposited on the semiconductor wafer, determining whether the measured thickness of the conductive layer is within a predetermined tolerance, and revising the deposition recipe if the thickness of the conductive layer is not within the predetermined tolerance. An apparatus includes a deposition unit capable of depositing a conductive layer according to a deposition recipe; a thickness measuring unit capable of measuring at least one thickness of the conductive layer and outputting thickness data; and a deposition control unit capable of receiving the thickness data from the thickness measuring unit, determining whether the thickness data is within a predetermined tolerance, revising the deposition recipe if the thickness data is not within the predetermined tolerance, and outputting the revised deposition recipe.